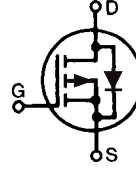


PolarP™ Power MOSFET

IXTR48P20P

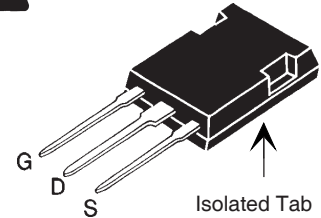
$$\begin{aligned} V_{DSS} &= -200V \\ I_{D25} &= -30A \\ R_{DS(on)} &\leq 93m\Omega \end{aligned}$$

P-Channel Enhancement Mode
Avalanche Rated



ISOPLUS247 (IXTR)

E153432



G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	- 200	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	- 200	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	- 30	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	-144	A
I_{AR}	$T_C = 25^\circ\text{C}$	- 48	A
E_{AS}	$T_C = 25^\circ\text{C}$	2.5	J
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	190	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10s	260	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1\text{mA}$	$t = 1\text{min}$ 2500 $t = 1\text{s}$ 3000	V~ V~
M_d	Mounting force	20..120 / 4.5..27	N/lb.
Weight		5	g

Features

- Silicon chip on Direct-Copper Bond (DCB) substrate
 - UL recognized package
 - Isolated mounting surface
 - 2500V electrical isolation
- Avalanche rated
- The rugged PolarP™ process
- Low Q_G
- Low Drain-to-Tab capacitance
- Low package inductance
 - easy to drive and to protect

Applications

- High side switching
- Push-pull amplifiers
- DC Choppers
- Automatic test equipment
- Load-Switch Application
- Fuel Injection Systems

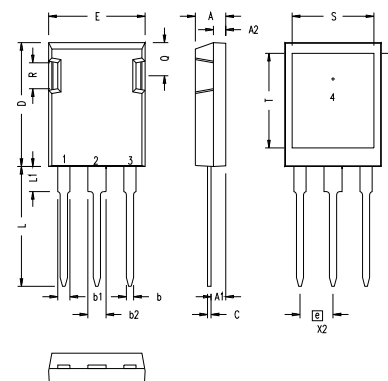
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = -250\mu\text{A}$	- 200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\mu\text{A}$	- 2.5		- 4.5 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			- 25 μA - 200 μA
$R_{DS(on)}$	$V_{GS} = -10V$, $I_D = -24A$, Note 1			93 m Ω

Symbol	Test Conditions (T _J = 25°C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = -10V, I _D = - 24A, Note 1	19	32	S
C_{iss}	$\left. \begin{array}{l} \\ \\ \end{array} \right\} V_{GS} = 0V, V_{DS} = - 25V, f = 1MHz$		5400	pF
C_{oss}			1040	pF
C_{rss}			170	pF
t_{d(on)}	$\left. \begin{array}{l} \\ \\ \\ \end{array} \right\} \textbf{Resistive Switching Times}$ $V_{GS} = -10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = - 24A$ $R_G = 3\Omega \text{ (External)}$		30	ns
t_r			46	ns
t_{d(off)}			67	ns
t_f			27	ns
Q_{g(on)}	$\left. \begin{array}{l} \\ \\ \end{array} \right\} V_{GS} = -10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = - 24A$		103	nC
Q_{gs}			23	nC
Q_{gd}			40	nC
R_{thJC}			0.15	0.66 °C/W
R_{thCS}				°C/W

Source-Drain Diode

Symbol (T _J = 25°C, unless otherwise specified)		Characteristic Values		
		Min.	Typ.	Max.
I _S	V _{GS} = 0V			- 48 A
I _{SM}	Repetitive, pulse width limited by T _{JM}			-192 A
V _{SD}	I _F = - 24A, V _{GS} = 0V, Note 1			- 3.3 V
t _{rr}	$\left. \begin{array}{l} I_F = - 24A, -di/dt = -150A/\mu s \\ V_R = -100V, V_{GS} = 0V \end{array} \right\}$		260	ns
Q _{RM}			4.2	μC
I _{RM}			- 32.2	A

ISOPLUS247 (IXTR) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - NO CONNECTION

NOTE: This drawing will meet all dimensions
requirement of JEDEC outline TO-247AD
except screw hole.

Note 1: Pulse test, $t \leq 300\mu s$; duty cycle, $d \leq 2\%$.

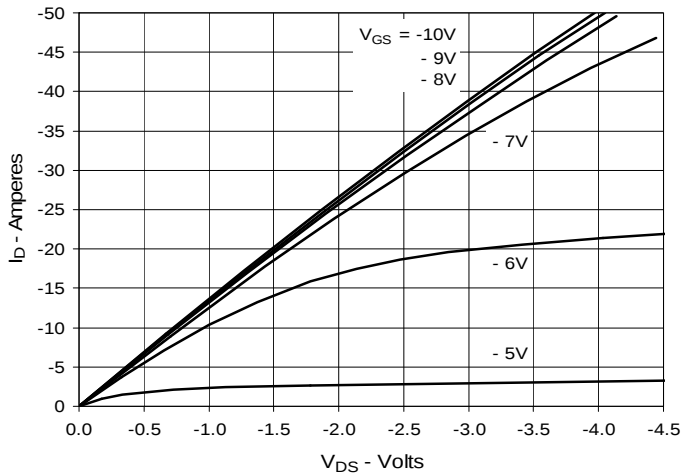
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

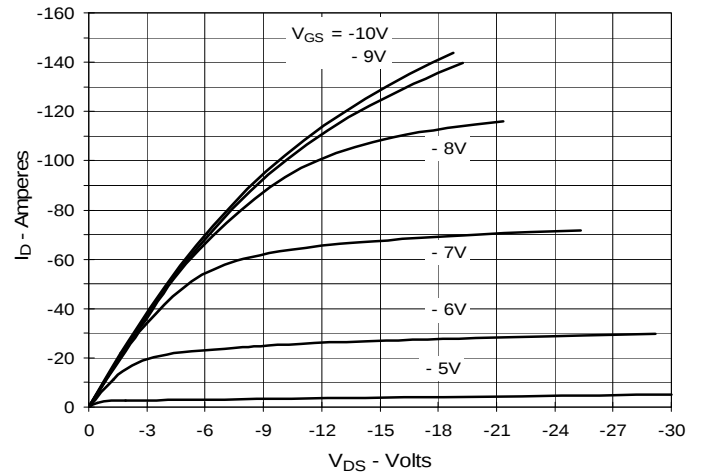
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

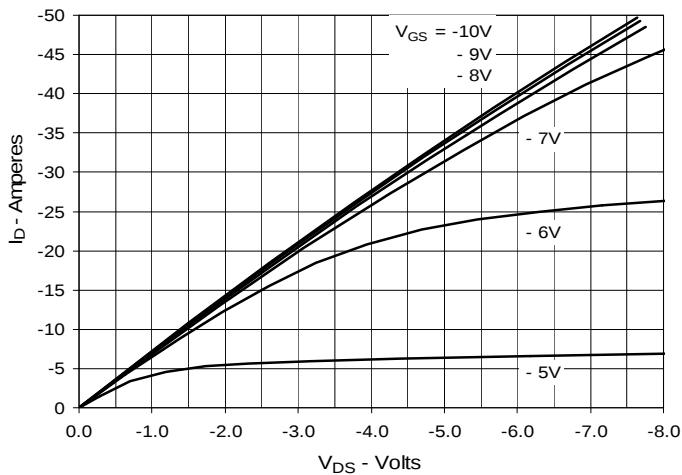
**Fig. 1. Output Characteristics
@ 25°C**



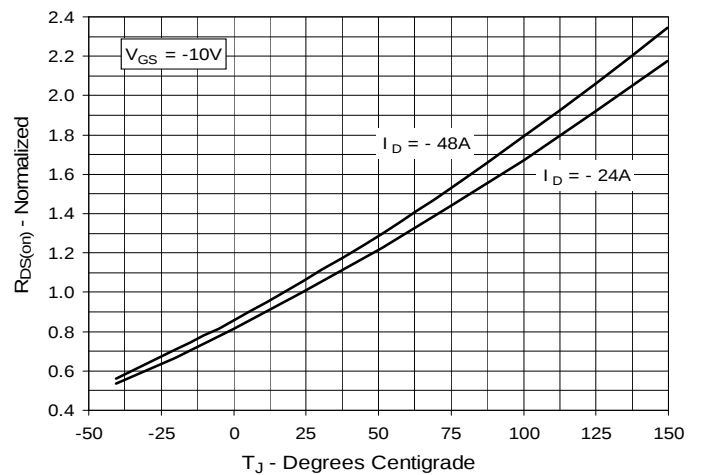
**Fig. 2. Extended Output Characteristics
@ 25°C**



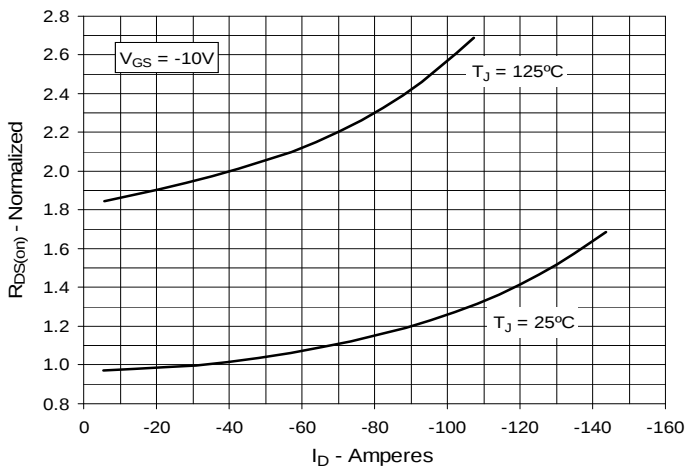
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = -24A$ vs.
Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = -24A$ vs.
Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

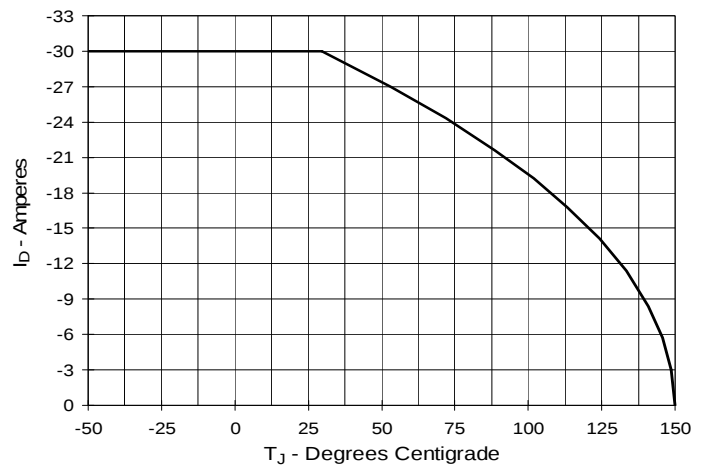


Fig. 7. Input Admittance

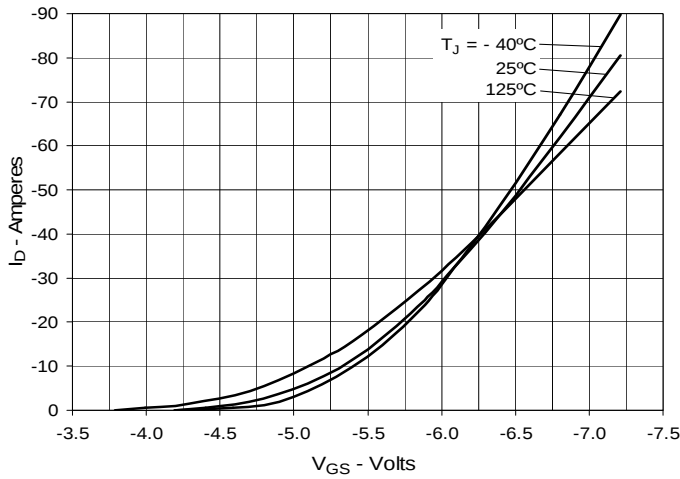


Fig. 8. Transconductance

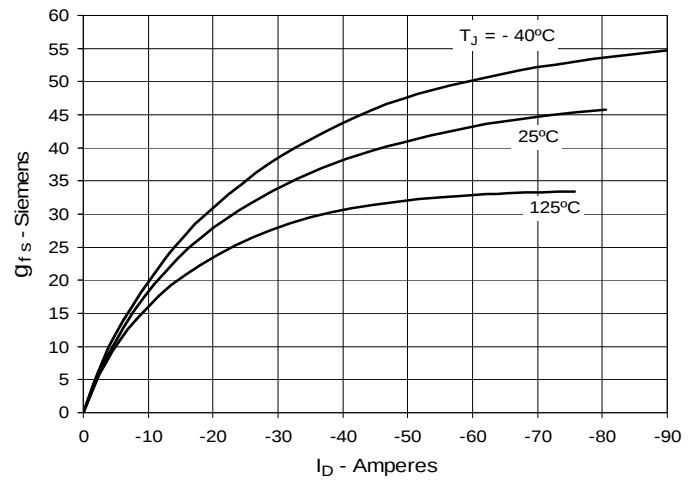


Fig. 9. Forward Voltage Drop of Intrinsic Diode

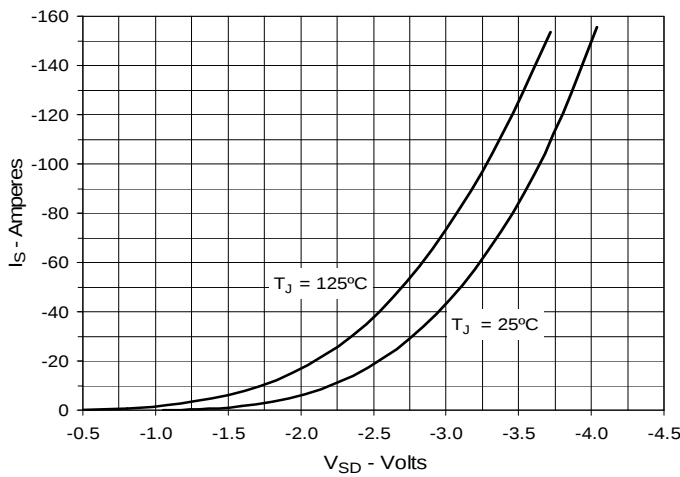


Fig. 10. Gate Charge

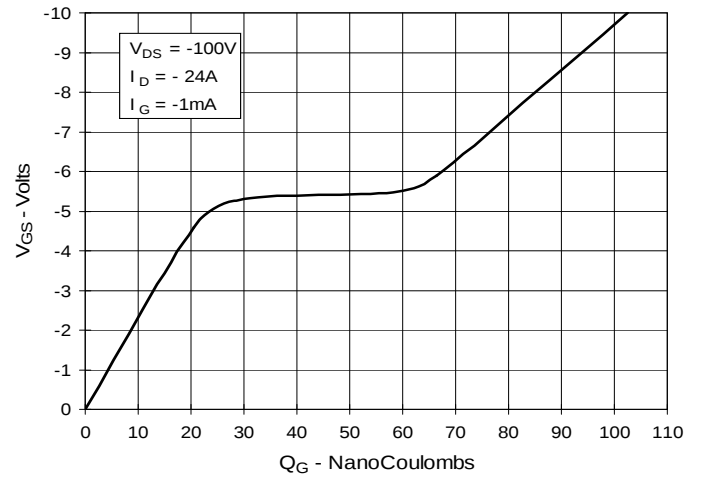


Fig. 11. Capacitance

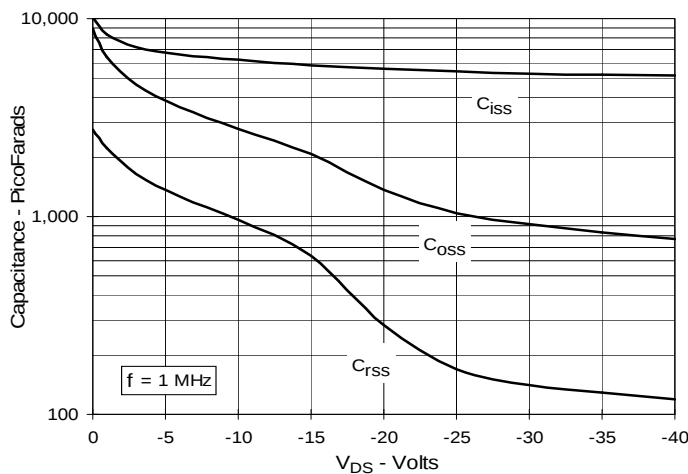


Fig. 12. Forward-Bias Safe Operating Area

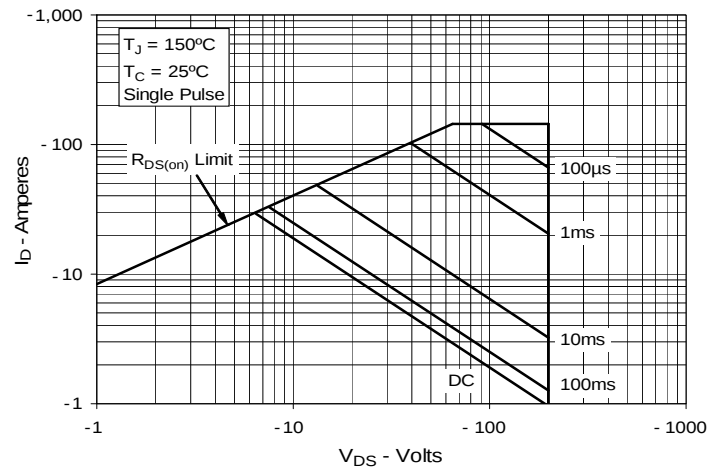


Fig. 13. Maximum Transient Thermal Impedance

